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### Esi Tronic 20131 Keygen EXCLUSIVE

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2. Description of the Related Art With the increasing degree of integration of DRAM cells, the design rule for dielectric isolation films has decreased to achieve more stable semiconductor devices. Therefore, the dielectric isolation film has been recently replaced with a thin film with a high dielectric constant that can solve the problems of defect increase and reduction of the margin for the source/drain junction leakage current, and also has a high breakdown voltage. Conventionally, the capacity of a capacitor (i.e., the source/drain junction area/dielectric thickness) has been increased in order to obtain sufficient capacitance using a conventional dielectric isolation film. In contrast, a thin film such as a Ta<sub>2</sub>O<sub>5</sub> film with a high dielectric constant has a high capacitance. However, if a conventional dielectric isolation film is replaced with a thin film having a high dielectric constant, the element isolation characteristic between the conventional capacitor and the transistor deteriorates. A thin film with a high dielectric constant, such as a Ta<sub>2</sub>O<sub>5</sub> film, has a high-quality oxide layer and a high crystallinity. However, it is difficult to obtain such a thin film with high quality using a conventional process. In addition, a thin film with high dielectric constant having a lot of defects can be formed from a conventional process such as oxidation. Therefore, a thin film of lower quality can be obtained. Laparoscopic enucleation and morcell

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